

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) An image reading device comprising:
a photoelectric conversion element having a photosensitive thin-film transistor and a capacitor connected to a drain electrode of the photosensitive thin-film transistor;
photoelectric conversion amount detecting means for detecting an amount of charge stored in the capacitor that varies according to intensity of light projected on the photosensitive thin-film transistor; and
control means for reversing the polarity of the stored charge in the capacitor with respect to a potential of a source electrode of the photosensitive thin-film transistor.
2. (Original) The image reading device as set forth in claim 1, wherein the control means reverses the polarity of the stored charge in the capacitor every image reading cycle or every multiple image reading cycles.
3. (Original) The image reading device as set forth in claim 1, wherein the photoelectric conversion amount detecting means includes a charge integration amplifier that detects charges of both positive and negative polarities.
4. (Original) The image reading device as set forth in claim 1, wherein the photoelectric conversion amount detecting means includes a charge integration amplifier that detects a charge of either positive or negative polarity.

5. (Original) The image reading device as set forth in claim 1, wherein, in order to reverse the polarity of the stored charge in the capacitor, the control means controls a voltage applied to an electrode of the capacitor opposite an electrode connected to the drain electrode of the photosensitive thin-film transistor.

6. (Original) The image reading device as set forth in claim 1, wherein:
the photoelectric conversion amount detecting means includes a charge integration amplifier; and

in order to reverse the polarity of the stored charge in the capacitor, the control means controls a reference voltage of the charge integration amplifier.

7. (Original) An image reading device comprising:
a photoelectric conversion element including a photosensitive thin-film transistor and a capacitor connected to a drain electrode of the photosensitive thin-film transistor;
a photoelectric conversion amount detecting section for detecting an amount of charge stored in the capacitor that varies according to intensity of light projected on the photosensitive thin-film transistor; and
a control section for reversing the polarity of the stored charge in the capacitor with respect to a potential of the source electrode of the photosensitive thin-film transistor.

8-13. (Canceled)

14. (New) The image reading device of claim 1, wherein the photoelectric conversion amount detecting means detects an amount of remaining charge stored in the capacitor that varies according to intensity of light projected on the photosensitive thin film transistor.

15. (New) The image reading device of claim 1, wherein the control means reverses the polarity of the previously stored charge in the capacitor.

16. (New) The image reading device of claim 1, wherein the control means is for reversing the polarity of the stored charge in the capacitor with respect to the potential of the source electrode of the photosensitive thin-film transistor so that the polarity of charge read out via a source line electrically connected to the source electrode is positive in certain reading cycles and negative in other reading cycles.

17. (New) The image reading device of claim 16, wherein the photoelectric conversion amount detecting means comprises a charge integration circuit whose output changes polarity every image reading cycle or every multiple image reading cycle for pixels receiving light.